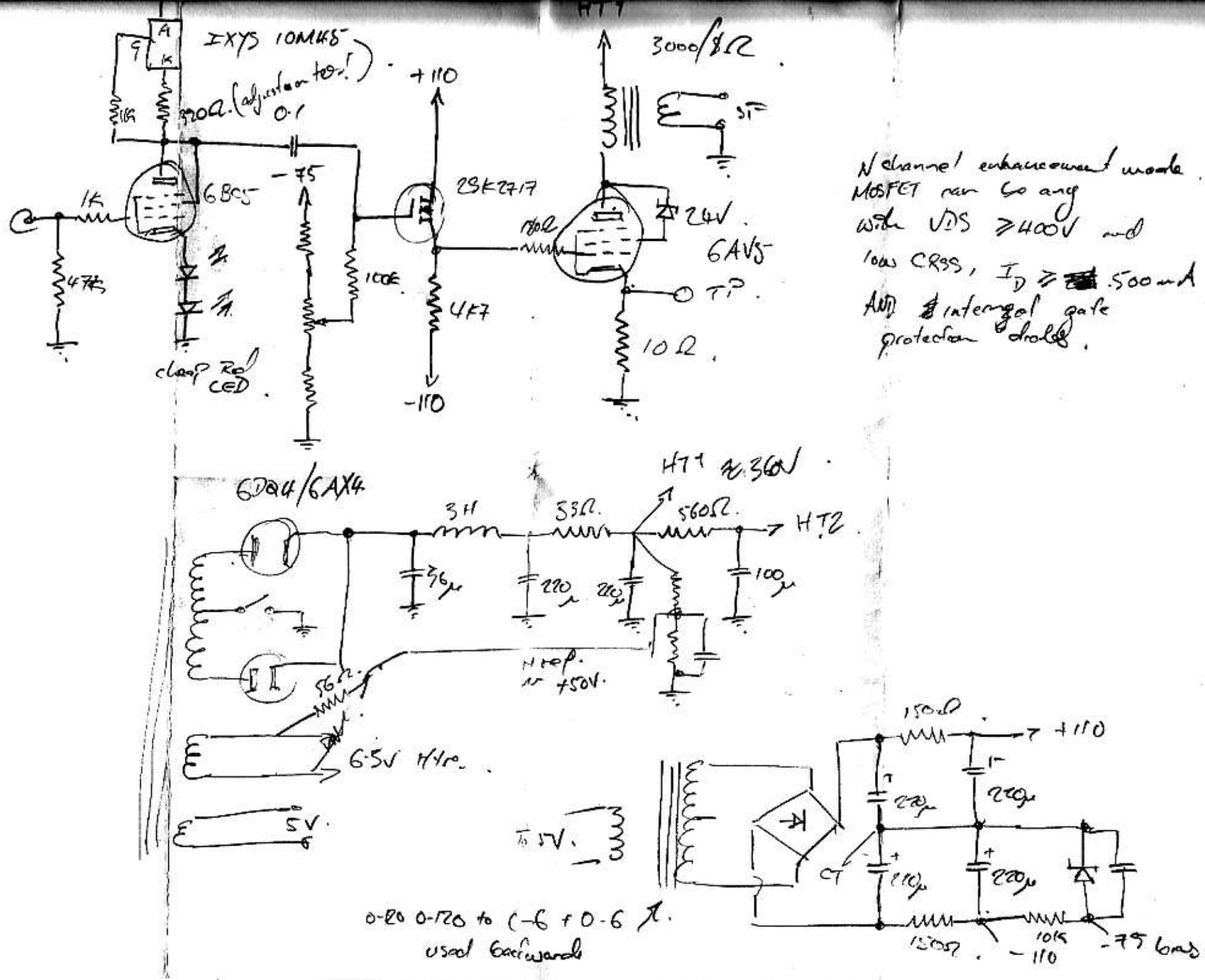

N channel enhancement mode MOSFET can be any with VDS ≥ 400V and low CRSS, I_D ≥ 500mA. AND internal gate protection diodes.